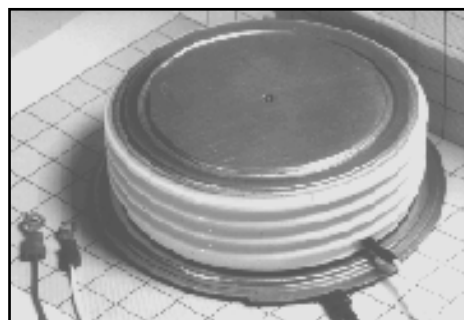


Description:

Powerex Silicon Controlled Rectifiers (SCR) are designed for phase control applications. These are all-diffused, hermetic Pow-R-Disc devices employing the field-proven amplifying gate.



Features:

- Low On-State Voltage
- High di/dt Capability
- High dv/dt Capability
- Excellent Surge and I²t Ratings

Applications:

- Power Supplies
- Battery Chargers
- Motor Controllers

Ordering Information

Select the complete 12 digit device part number from the table below.

Type	Voltage V _{DRM} V _{RRM}	Current I _{T(av)}	Turn-Off t _q	Gate Current I _{GT}	Lead Code
TBS7	12	32	0	3	DH
	14				
	16				
	1200 V	3200 A	350 μs typical	200 mA	12"
	1400 V				
	1600 V				

Absolute Maximum Ratings

Characteristics	Symbol		Units
Non-repetitive Transient Peak Reverse Voltage	V_{RSM}	$V_{RRM}+100V$	V
RMS On-State Current	$I_{T(RMS)}$	5025	A
Average Current 180° Sine Wave, $T_C=76^{\circ}C$	$I_{T(AV)}$	3200	A
Peak One Cycle Surge On-State Current (Non-Repetitive) 60Hz	I_{TSM}	44,000	A
Peak One Cycle Surge On-State Current (Non-Repetitive) 50Hz	I_{TSM}	40500	A
Critical Rate-of-Rise of On-State Current (Non-Repetitive)	di/dt	300	A/ μs
Critical Rate-of-Rise of On-State Current (Repetitive)	di/dt	100	A/ μs
I^2t for Fusing for One Cycle, 60 Hz	I^2t	8.07×10^6	A ² s
Peak Gate Power Dissipation	P_{GM}	250	W
Average Gate Power Dissipation	$P_{G(av)}$	35	W
Operating Temperature	T_J	-40 to 125°C	°C
Storage Temperature	T_{STG}	-40 to 150°C	°C
Mounting Force		6000 to 10000 26.6 to 44.4	lb. kN

TBS716P13.DOC.1/19/2006

Information presented is based upon manufacturers testing and projected capabilities. This information is subject to change without notice. The manufacturer makes no claim as to suitability for use, reliability, capability or future availability of this product.

Electrical Characteristics, $T_J=25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Repetitive Peak Reverse Leakage Current	I_{RRM}	$T_J=125^\circ\text{C}$, $V_R=V_{RRM}$			150	mA
Repetitive Peak Forward Leakage Current	I_{DRM}	$T_J=125^\circ\text{C}$, $V_D=V_{DRM}$			150	mA
Peak On-State Voltage	V_{TM}	$T_J=25^\circ\text{C}$, $I_{TM}=3000\text{A}$ Duty Cycle < 0.01%			1.25	V
Threshold Voltage, Low-level	$V_{(TO)1}$	$T_J=125^\circ\text{C}$, for $500\text{A} \leq I_{TM} < 10,000\text{A}$			0.776	V
Slope Resistance, Low-level	r_{T1}				0.0889	m Ω
Threshold Voltage, High-level	$V_{(TO)2}$	$T_J=125^\circ\text{C}$, for $I_{TM} < 10,000\text{A}$			1.032	V
Slope Resistance, High-level	r_{T2}				0.0735	m Ω
ABCD V_{TM} Modeling Coefficients	A	$T_J=125^\circ\text{C}$, for $500\text{A} \leq I_{TM} < 60,000\text{A}$			0.7393	V
	B				-0.01883	-
	C				0.05747	m Ω
	D				0.005836	-
Typical Delay Time	t_d	$I_{TM}=1000\text{A}$, $V_D=0.5V_{DRM}$		3		μs
Maximum Turn-Off Time	t_q	$T_J=125^\circ\text{C}$, $I_T=1000\text{A}$, $di_R/dt=25\text{A}/\mu\text{s}$ $dv/dt=20\text{V}/\mu\text{s}$ linear to 80% V_{DRM}		350		μs
Minimum Critical dv/dt - Exponential to V_{DRM}	dv/dt	$T_J=125^\circ\text{C}$	300			V/ μs
Gate Trigger Current	I_{GT}	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$			200	mA
Gate Trigger Voltage	V_{GT}	$T_J=25^\circ\text{C}$, $V_D=12\text{V}$			4.0	V
Non-Triggering Gate Voltage	V_{GDM}	$T_J=125^\circ\text{C}$, $V_D=V_{DRM}$			0.5	V
Peak Forward Gate Current	I_{GTM}				4	A
Peak Reverse Gate Voltage	V_{GRM}				10	V

Thermal Characteristics

Characteristics	Symbol	Min.	Typ.	Max.	Units
Maximum Thermal Resistance, Double Sided Cooling					
Junction to Case	$R_{\theta JC}$.010	$^\circ\text{C}/\text{W}$
Case to Sink	$R_{\theta CS}$.002	$^\circ\text{C}/\text{W}$